

# Silicon Carbide (SiC) Schottky Diode – EliteSiC, 40 A, 650 V, D1, TO-247-3L

## FFSH4065ADN-F155

### Description

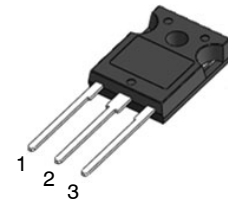
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

### Features

- Max Junction Temperature 175°C
- Avalanche Rated 95 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- This Device is Pb-Free and is RoHS Compliant

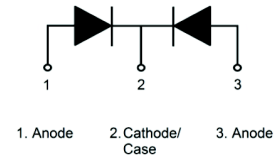
### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



TO-247-3LD  
CASE 340CH

$V_{RRM}$	$I_F$
650 V	40 A



### MARKING DIAGRAM



A	= Assembly Plant Code
YWW	= Date Code (Year & Week)
ZZ	= Lot Traceability Code
FFSH4065ADN	= Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FFSH4065ADN-F155

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, Unless otherwise specified)

Symbol	Parameter		FFSH4065ADN-F155	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage		650	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		95	mJ
I <sub>F</sub>	Continuous Rectified Forward Current	@T <sub>C</sub> < 140°C	20* / 40**	A
	Continuous Rectified Forward Current	@ T <sub>C</sub> < 135°C	22* / 44**	
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	1100	A
		T <sub>C</sub> = 150°C, 10 μs	1000	A
I <sub>F, SM</sub>	Non-Repetitive Forward Surge Current		105	A
I <sub>F, RM</sub>	Repetitive Forward Surge Current		58	A
P <sub>tot</sub>	Power Dissipation	T <sub>C</sub> = 25°C	150	W
		T <sub>C</sub> = 150°C	25	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
	TO247 Mounting Torque, M3 Screw		60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

\*Per leg.

\*\*Per Device.

1. E<sub>AS</sub> of 95 mJ is based on starting T<sub>J</sub> = 25°C, L = 0.5 mH, I<sub>AS</sub> = 19.5 A, V = 50 V.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Rating	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case, Max.	1.0* / 0.5**	°C/W

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 20 A, T <sub>C</sub> = 25°C	–	1.5	1.75	V
		I <sub>F</sub> = 20 A, T <sub>C</sub> = 125°C	–	1.6	2.0	
		I <sub>F</sub> = 20 A, T <sub>C</sub> = 175°C	–	1.72	2.4	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 650 V, T <sub>C</sub> = 25°C	–	–	200	μA
		V <sub>R</sub> = 650 V, T <sub>C</sub> = 125°C	–	–	400	
		V <sub>R</sub> = 650 V, T <sub>C</sub> = 175°C	–	–	600	
Q <sub>C</sub>	Total Capacitance Charge	V = 400 V	–	64	–	nC
C	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	–	1085	–	pF
		V <sub>R</sub> = 200 V, f = 100 kHz	–	117	–	
		V <sub>R</sub> = 400 V, f = 100 kHz	–	88	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSH4065ADN-F155	FFSH4065ADN	TO-247-3LD	30 Units / Tube

## TYPICAL CHARACTERISTICS

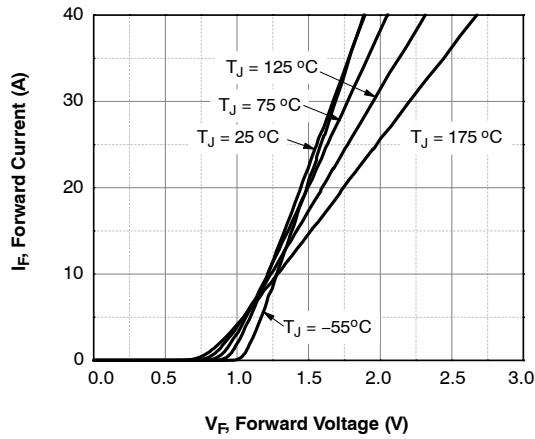
(T<sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)

Figure 1. Forward Characteristics

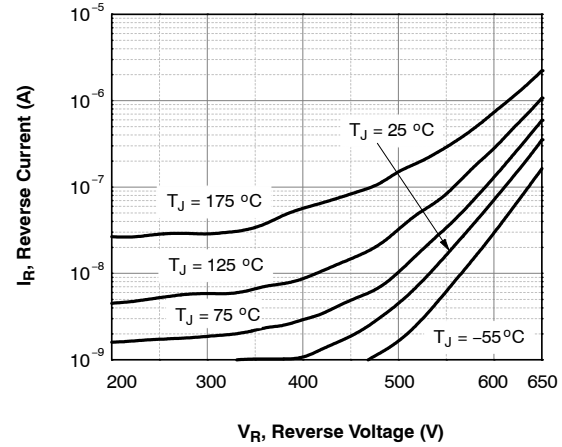


Figure 2. Reverse Characteristics

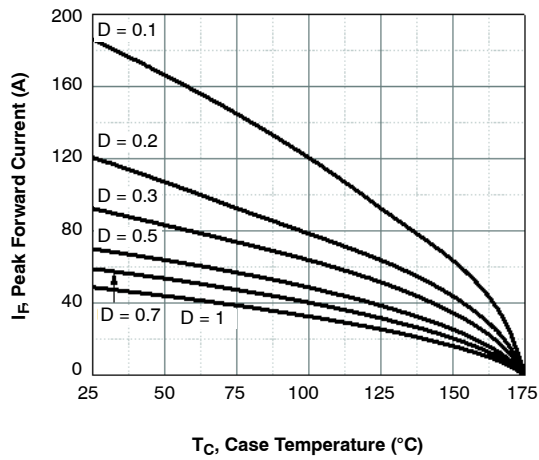


Figure 3. Current Derating

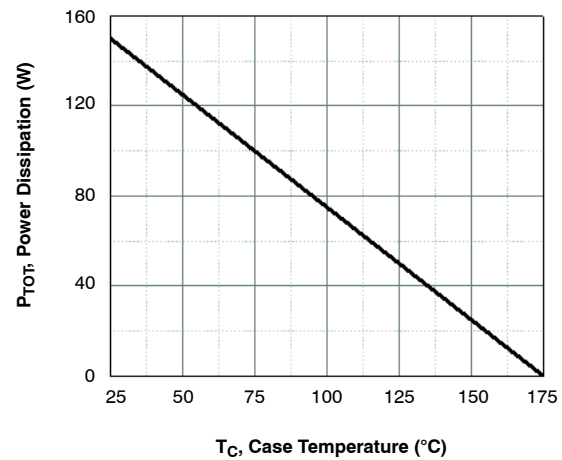


Figure 4. Power Derating

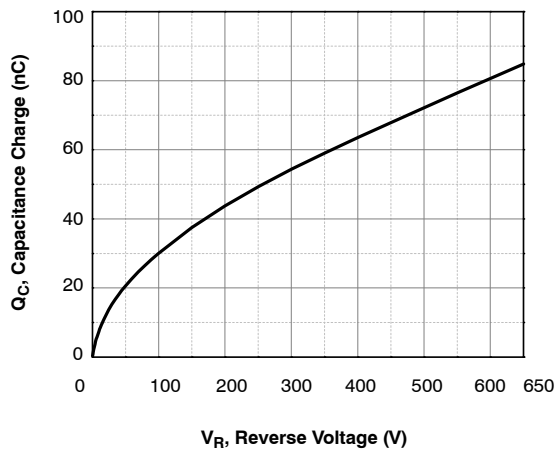


Figure 5. Capacitive Charge vs. Reverse Voltage

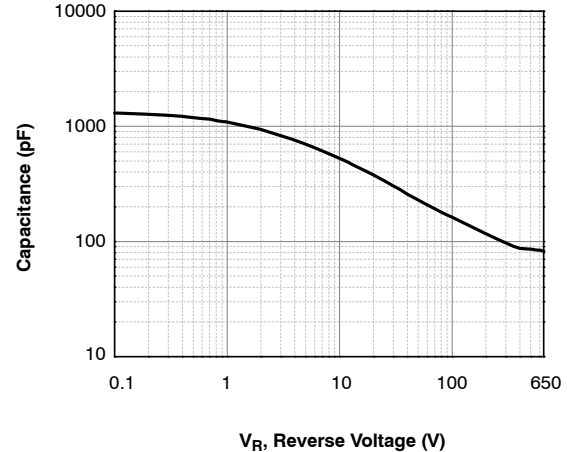


Figure 6. Capacitance vs. Reverse Voltage

## TYPICAL CHARACTERISTICS (CONTINUED)

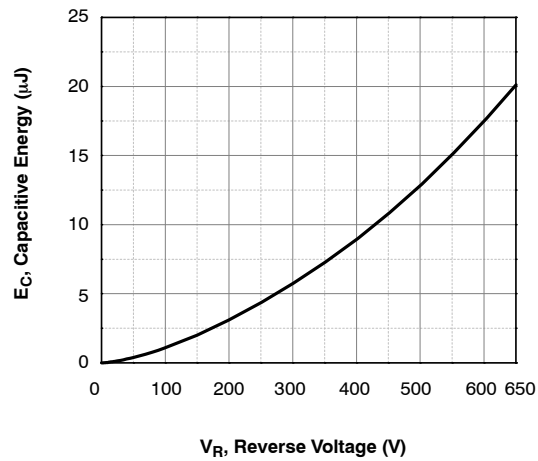
(T<sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)

Figure 7. Capacitance Stored Energy

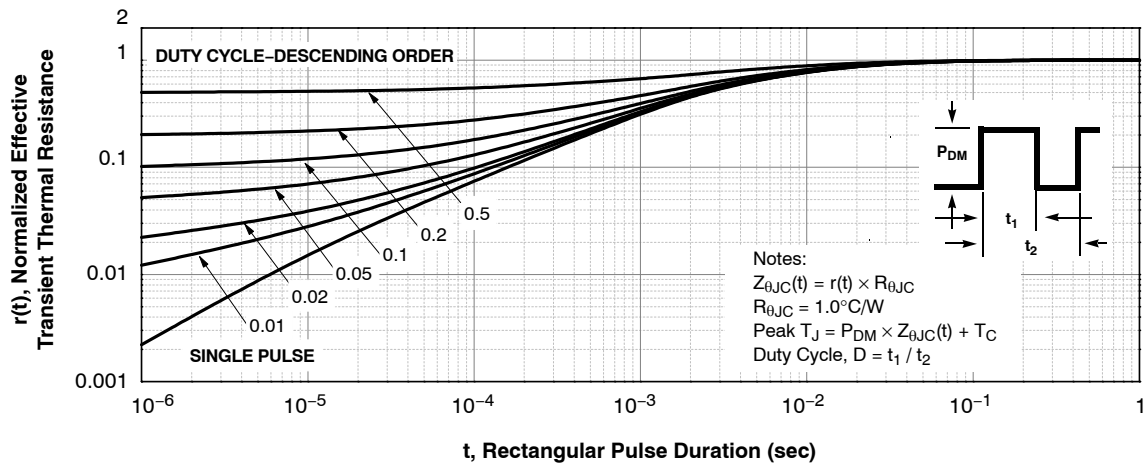


Figure 8. Junction-to-Case Transient Thermal Response Curve

## TEST CIRCUIT AND WAVEFORMS

$L = 0.5 \text{ mH}$   
 $R < 0.1 \Omega$   
 $V_{DD} = 50 \text{ V}$   
 $E_{AVL} = 1/2 L I_L^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$   
 $Q1 = \text{IGBT } (BV_{CES} > DUT V_{R(AVL)})$

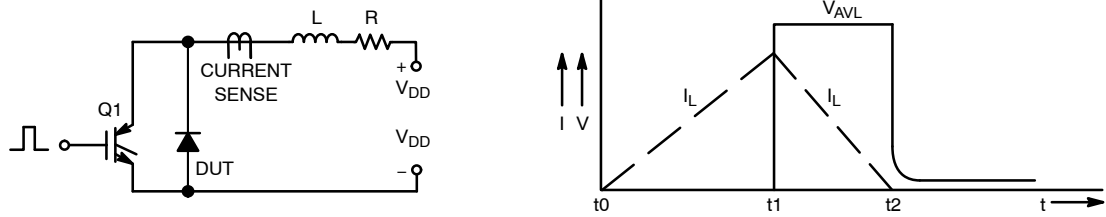
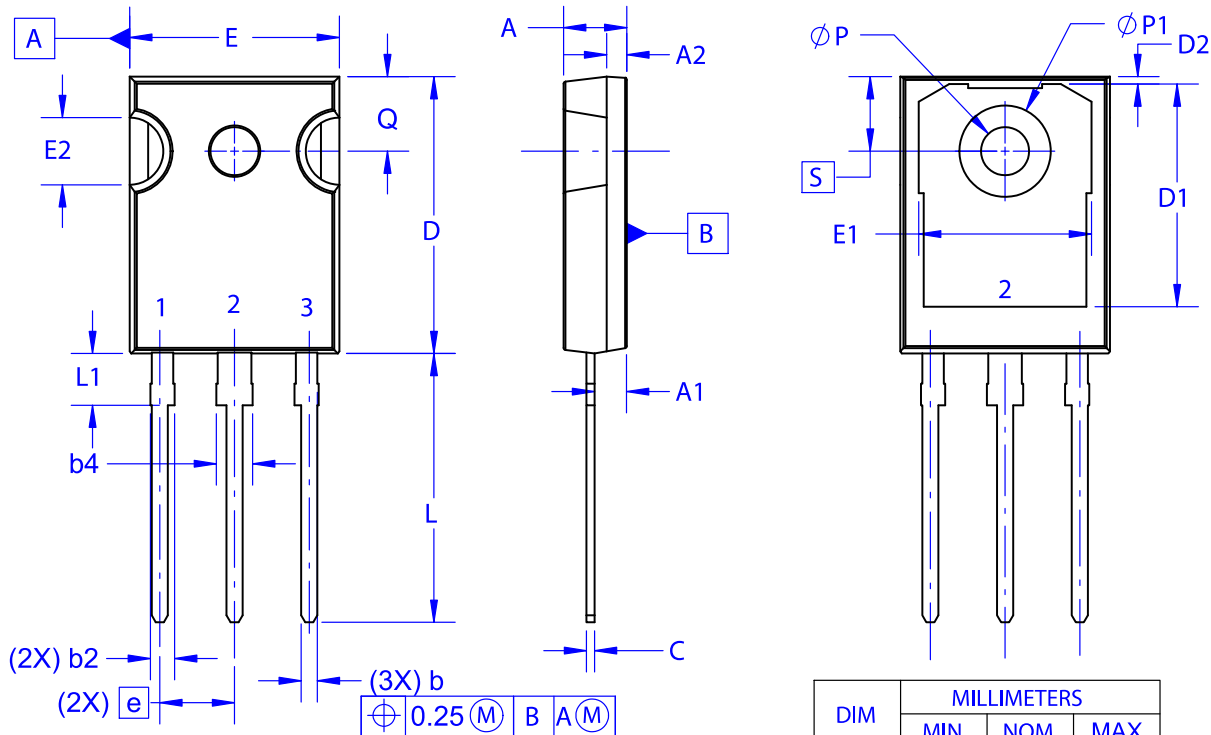


Figure 9. Unclamped Inductive Switching Test Circuit &amp; Waveform

TO-247-3LD  
CASE 340CH  
ISSUE A

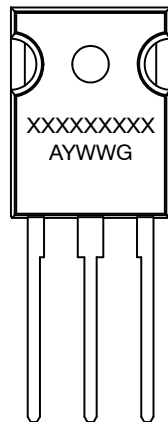
DATE 09 OCT 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC  
MARKING DIAGRAM\*



XXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.29	2.475	2.66
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
$\phi P$	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
$\phi P1$	6.61	6.73	6.85

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